I hereby certify that this correspondence is being deposited via first class mail with the United States Postal Service addressed to: Commissioner of Patents and Trademarks, Alexandria, VA 22313, on September 29, 2005.

The applicant and/or attorney requests the date of deposit as the filing date.

Depositor: Robert Faber Nicole Garrese

40 (Signature & date) Nuccel Barr

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

かre application of

OCT 0 8 2005

September 26, 2005

Cheng, et al.

Group Art Unit: 2812

Serial No: 10/710,608

Examiner: Tara Washington

Filed: 7/23/04

International Business Machines Corporation

IFUI

2070 Route 52

Hopewell Junction, NY 12533

**TITLE:** Patterned Strained Semiconductor Substrate and Device

## **INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to the duty of disclosure set forth in 37 C.F.R. 1.56, and further pursuant to the provisions of 37 C.F.R. 1.97 and 1.98, applicants hereby respectfully submit copies of the US and non-US patents and publications as listed on Form PTO-1449, attached hereto.

In citing these documents, no representation is made nor intended as to the pertinency or nonpertinency of the art, that better art than that listed is not available, or that other art is not applicable.

No fee is believed to be due for this submission. If any fees are required, however, the Commissioner is hereby authorized to charge such fees to Deposit Account No. 09-0458.

Respectfully submitted, Cheng, et al.

Joseph P. A

Registration No. 30,238

Telephone No. 845-894-4633

FIS920040150US1

`	10F	PRIMATION DISCLOSUR	RE CITATION		Docket Number (Optional) FIS920040150US1 Applicant(s)	Application Number 10/710,608			
		(Ove several sheets if neces	isary)		Cheng, et al.				
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		4,665,415	5-12-87	Esaki,	et al.				
		4,853,076	8-1-89	Tsaur,	et al.				
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		4,952,524	8-28-90	Lee, et	al.				
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		US 2001/0009784 A1	7-26-01	Ma, et a	ıl.				
		US 2002/0063292 A1	5-30-02	Armstr	ong, et al.				
		US 2002/0074598 A1	6-20-02	Doyle, e	t al.				
		US 2002/0086472	7-4-02	Roberd	s, et al.				
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		JP64-76755	03-1989	Japan					
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		Kern Rim, et al., "Trander Devices Meeting, 26, 8,	nsconductance E 1, IEEE, Septen	nhancement nber 1998.	in Deep Submicron St	trained-Si n-MO	SFETs". Intern	ational El	ectron
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		4,958,213	9-18-90	Eklund	, et al.				
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-		5,060,030	10-22-91	Hoke, e	t al.				
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		US 2002/0086497 A1	7-4-02	Kwok				IF AFF	ROPRIATE
		US 2002/0090791 A1	7-11-02	Doyle, et	al.				
	US 2003/0032261 A1 2-13-03		Yeh, et a	1.					
		US 2003/0040158 A1	2-27-03	Saitoh					
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		P.O.A. I. A. T. T.							
		F. Ootsuka, et al., "A H Application." Internation	ighly Dense, High onal Electron De	h-Performan vices Meetin	ce 130nm Node CMC g, 23.5.1, IEEE, Apri	S Technology fo I 2000.	r Large Scale Sy	/stem-on-	a-Chip
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		5,134,085	7-28-92	Gilgen,	et al.					
		5,310,446	5-10-94	Konishi	i, et al.					
		5,354,695	10-11-94	Leedy						7
		5,371,399	12-6-94	Burrou	ghes, et al.					
		5,391,510	2-21-95	Hsu, et	al.					
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		US 2003/0057184 A1	3-27-03	Yu, et a	1.					
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		Shinya Ito, et al., "Med International Electron	chanical Stress E Devices Meeting	ffect of Etch , 10.7.1, IEE	-Stop Nitride and its l EE, April 2000.	Impact on Deep S	ubmicron Tran	sistor Des	ign."	
		A. Shimizu, et al., "Loc International Electron	cal Mechanical-S Devices Meeting	tress Contro , IEEE, Mai	ol (LMC): A New Tech rch 2001.	nnique for CMOS	-Performance l	Enhancem	ent."	
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Application Number

Form PTO-A820 (also form PTO-1449) P09A/REV05

Patent and Trademark Office \* U.S. DEPARTMENT OF

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*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE		NAME	CLASS	SUBCLASS		NG DATE ROPRIATE	
		5,459,346	10-17-95	Asakaw	/a, et al.					
		5,471,948	12-5-95	Burrou	ghes, et al.					
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		5,561,302	10-1-96	Candela	aria					
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		K. Ota, et al., "Novel L Devices Meeting, 2.2.1,	Locally Strained ( , IEEE, Februar	Channel Tec y 2002.	hnique for High Perfo	)rmance 55nm C	MOS." Interna	tional Ele	ctron	
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		G. Zhang, et al., "A Ne IEEE Transactions on	w 'Mixed-Mode' Electron Devices	Reliability , vol. 49, no.	Degradation Mecnanis . 12, December 2002, p	sm in Advanced app. 2151-56.	Si and SiGe Bipe	olar Trans	sistors."	
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## Application Number Docket Number (Optional) FIS920040150US1 10/710,608 Applicant(s) INFORMATION DISCLOSURE CITATION Cheng, et al. (Use several sheets if necessary) Group Art Unit Filing Date 7/23/04 2812 **U.S. PATENT DOCUMENTS \*EXAMINER** FILING DATE REP DATE NAME **CLASS SUBCLASS** DOCUMENT NUMBER INITIAL IF APPROPRIATE 11-5-96 5,571,741 Leedy 1-7-97 5,592,007 Leedy 1-7-97 5,592,018 Leedy 5,670,798 9-23-97 Schetzina 10-21-97 5,679,965 Schetzina U.S. PATENT APPLICATION PUBLICATIONS \*EXAMINER FILING DATE **SUBCLASS** DATE NAME **CLASS** REF DOCUMENT NUMBER INITIAL IF APPROPRIATE FOREIGN PATENT DOCUMENTS Translation **COUNTRY SUBCLASS CLASS** REF DATE DOCUMENT NUMBER YES NO (Including Author, Title, Date, Pertinent Pages, Etc.) **OTHER DOCUMENTS** H.S. Momose, et al., "Temperature Dependence of Emitter-Base Reverse Stress Degradation and its Mechanism Analyzed by MOS Structures." Paper 6.2, pp. 140-143. C.J. Huang, et al., "Temperature Dependence and Post-Stress Recovery of Hot Electron Degradation Effects in Bipolar Transistors." IEEE 1991 Bipolar Circuits and Technology Meeting 7.5, pp. 170-173.

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		5,683,934	11-4-97	Candel	aria				
		5,840,593	11-24-98	Leedy					_
		5,861,651	1-19-99	Brasen,	et al.				
		5,880,040	3-9-99	Sun, et	al.				
		5,940,716	8-17-99	Jin, et a	nl.				
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		S.R. Sheng, et al., "De		DOCUMEN			t Carrier Stress		14.15
		S.R. Sheng, et al., De	gradadon and Ive	covery of Si	Ge HD 13 Following R	adiation and II		ing. i þ.	14-15.
		Z. Yang, et al., "Avala Transistors." Pp. 1-5.	nche Current Inc	duced Hot C	arrier Degradation in	200 GHz SiGe I	leterojunction B	ipolar	
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		5,940,736	8-17-99	Brady,	et al.				
		5,946,559	8-31-99	Leedy					
		5,960,297	9-28-99	Saki					
		5,989,978	11-23-99	Peidous	S				
		6,008,126	12-28-99	Leedy					
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	$\top$	H. Li, et al., "Design of	f W-Band VCOs	with High (	Output Power for Potenti			•	lar
		Systems. Augustall	Oans Diguss pp.	. 205-00.					
	-	H. Wurzer, et al., "And Devices, vol. 41, no. 4.	nealing of Degrad	ded npn-Tra	ansistors- Mechanisms ar	nd Modeling." I	EEE Transact	ions on Ele	ctron
		Devices, von 12, 201 1, 2	whin 1994) ble c	33-3 <b>0.</b>					
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Form PTO-A820 (also form PTO-1449)

Application Number

## Docket Number (Optional) **Application Number** 10/710,608 FIS920040150US1 INFORMATION DISCLOSURE CITATION Applicant(s) Cheng, et al. (Use several sheets if necessary) Filing Date Group Art Unit 7/23/04 2812 **U.S. PATENT DOCUMENTS** EXAMINER FILING DATE REF DOCUMENT NUMBER DATE **CLASS SUBCLASS** NAME INTTIAL IF APPROPRIATE 6,025,280 2-15-00 Brady, et al. 6,046,464 4-4-00 Schetzina 6,066,545 5-23-00 Doshi, et al. 6,090,684 Ishitsuka, et al. 7-18-00 6,107,143 8-22-00 Park, et al. U.S. PATENT APPLICATION PUBLICATIONS \*EXAMINER **FILING DATE** REF DOCUMENT NUMBER DATE NAME **CLASS SUBCLASS** INITIAL IF APPROPRIATE FOREIGN PATENT DOCUMENTS Translation REF DOCUMENT NUMBER DATE COUNTRY **SUBCLASS CLASS** YES NO **OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.) B. Doyle, et al., "Recovery of Hot-Carrier Damage in Reoxidized Nitrided Oxide MOSFETs." IEEE Electron Device Letters, vol. 13, no. 1, January 1992, pp. 38-40. H.S. Momose, et al., "Analysis of the Temperature Dependence of Hot-Carrier-Induced Degradation in Bipolar Transistors for Bi-CMOS." IEEE Transactions on Electron Devices, vol. 41, no. 6, June 1994, pp. 978-987.

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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		6,117,722	9-12-00	Wuu, et	t al.				
		6,133,071	10-17-00	Nagai					
		6,165,383	12-26-00	Chou					
		6,221,735	4-24-01	Manley	/, et al.				
		6,228,694	5-8-01	Doyle, e	et al.			·	
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		J.C. Bean, et al., Epitaxy". J. Vac.	"GEx SI 1-1 Sci. Techno	x/S1 Strai ol. A 2(2)	ined-Layer Superla ), AprJune 1984	attice Grown b , pp. 436-440.	y Molecular	Beam	
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		6,255,169	7-3-01	Li, et al	•				
		6,261,964	7-17-01	Wu, et a	al.				
		6,265,317	7-24-01	Chiu, et	t al.				•••
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		J.W. Matthews, et (1974), pp. 118-1	t al., "Defec 125.	ts in Epit	axial Multilayers	s". Journal	of Crystal Gr	owth 27	
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		6,284,623	9-4-01	Zhang,	et al.					
		6,284,626	9-4-01	Kim						
		6,319,794	11-20-01	Akatsu,	, et al.					
		6,361,885	3-26-02	Chou					,,,,,	
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		6,403,486	6-11-02	Lou			c			
		6,403,975	6-11-02	Brunne						
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		6,501,121	12-31-02	Yu, et al.					OIRIAI		
		6,506,652	1-14-03	Jan, et al	•						
		6,509,618	1-21-03	Jan, et al							
		6,521,964	2-18-03	Jan, et al	•						
		6,531,369	3-11-03	Ozkan, et	t al.						
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		6,531,740	3-11-03	Bosco,	Bosco, et al.					
		6,621,392	9-16-03	Volant,	et al.					
		6,635,506	10-21-03	Volant,	Volant, et al.					
		6,831,292	12-14-04	Currie	, et al.					
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